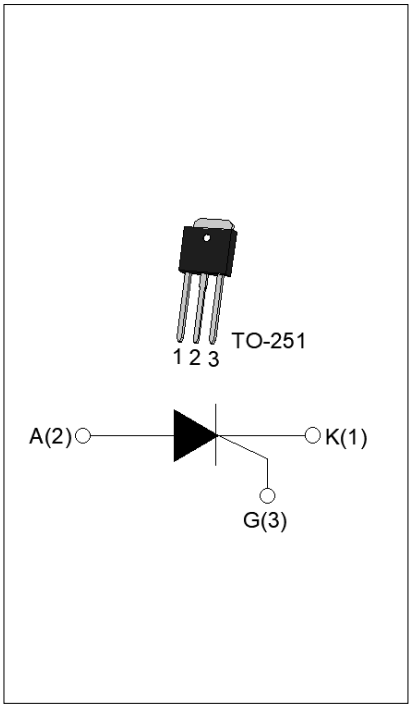
JCT151H-800R 12A SCR Rev.A.1.1

DESCRIPTION:

With high ability to withstand the shock loading of large current, JCT151H-800R of silicon controlled rectifiers provides high dV/dt rate with strong resistance to electromagnetic interference. It is especially recommended for use on solid state relay, motorcycle, power charger, T-tools etc. Package TO-251 is RoHS compliant.



MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	12	A
V_{DRM}/V_{RRM}	800	V
I_{GT}	”15	mA

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	
Operating junction temperature range	T_j	-40-125	
Repetitive peak off-state voltage (T_j=25)	V_{DRM}	800	V
Repetitive peak reverse voltage (T_j=25)	V_{RRM}	800	V
Average on-state current (T_C 0 49)	$I_{T(AV)}$	7.5	A
RMS on-state current (T_C 049)	$I_{T(RMS)}$	12	A
Non repetitive surge peak on-state current (t_p=10ms, T_j=25)	I_{TSM}	120	A
Non repetitive surge peak on-state current (t_p=8.3ms, T_j=25)		132	
I^2t value for fusing (t_p=10ms , T_j=25)	I^2t	72	A^2s
Critical rate of rise of on-state current (I_G=2× I_{GT}, f=100Hz , T_j=125)	dI/dt	100	A s
Peak gate current (t_p=20 s , T_j=125)	I_{GM}	4	A

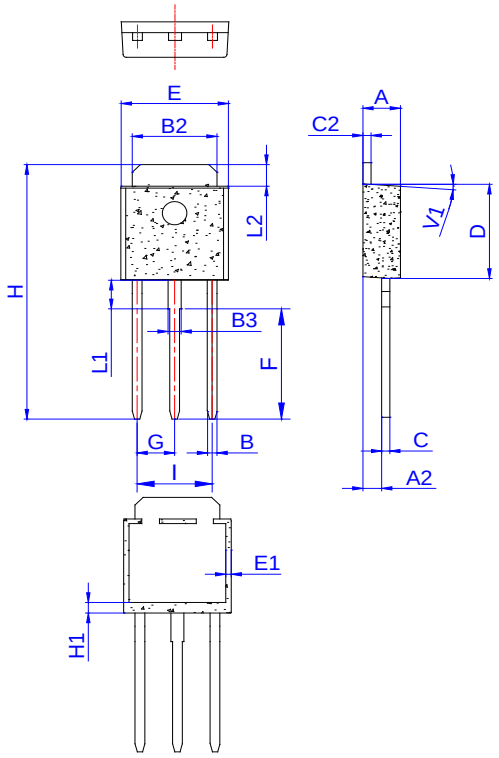
JCT151H-800R Jie Jie M

FIG.1: Maximum power dissipation versus RMS on-state current

FIG.2: RMS on-state current versus case temperature

FIG.7 ÖTest circuit for inductive and resistive loads to IEC-61000-4-5 standards.

PACKAGE MECHANICAL DATA 0.1 0.2 0.0390.00.0.34 -8.594 -1.506 0 Td [(1)8028



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.20		2.40	0.086		0.095
A2	1.00		1.30	0.039		0.051
B	0.50		0.70	0.020		0.028
B2	5.10		5.40	0.200		0.213
B3	0.70		1.00	0.028		0.039
C	0.45		0.62			
C2	0.48					
D						
E	6.40		6.70	0.252		0.264
E1	0.60		1.00	0.024		0.039
F	6.90		7.30	0.272		0.287
G	2.20			0.087		
H	16.00		17.00	0.630		0.669
H1	1.45		1.85	0.057		0.073
I	4.40		4.80	0.173		0.189
L1						
L2	1.25		1.55		1.00	
V1						

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